

MOSFET – Power, P-Channel, SOT-23

-20 V, -400 mA

NTR0202PL, NVTR0202PL

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life R_{DSon} = 0.80 Ω , V_{GS} = -10 V R_{DSon} = 1.10 Ω , V_{GS} = -4.5 V
- Miniature SOT-23 Surface Mount Package Saves Board Space
- NVT Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- DC-DC Converters
- Computers
- Printers
- PCMCIA Cards
- · Cellular and Cordless Telephones

MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted)

Symbol	Rating	Value	Unit
V _{DSS}	Drain-to-Source Voltage	-20	V
V _{GS}	Gate-to-Source Voltage - Continuous	±20	V
I _D I _{DM}	Continuous Drain Current @ T_A = 25 °C Pulsed Drain Current ($t_p \le 10 \mu s$)	-0.4 -1.0	Α
P _D	Total Power Dissipation @ T _A = 25 °C (Note 1)	225	mW
T _J , T _{stg}	Operating and Storage Temperature Range	– 55 to 150	°C
$R_{\theta JA}$	Thermal Resistance - Junction-to-Ambient	556	°C/ W
I _S	Source Current (Body Diode)	0.4	Α
TL	Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 s	260	°C

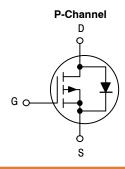
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

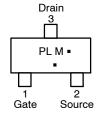
V _{(BR)DSS}	V _{(BR)DSS} R _{DS(on)} Typ		V _{(BR)DSS} R _{DS(on)} Typ I _D MAX	
-20 V	550 mΩ @ –10 V	–400 mA		



SOT-23 CASE 318 STYLE 21



MARKING DIAGRAM & PIN ASSIGNMENT



PL = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

 For additional marking information, refer to Application Note <u>AND8002/D</u>.

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 4.

ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

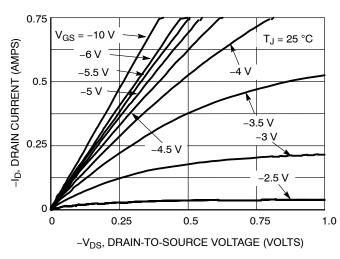
Symbol	Characteristic			Тур	Max	Unit
OFF CHAP	RACTERISTICS		•			
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage $(V_{GS}=0\ V,\ I_D=-10\ \mu A)$ (Positive Temperature Coefficient)			33		V mV/°C
I _{DSS}	Zero Gate Voltage Drain Current ($V_{DS}=-20$ V, $V_{GS}=0$ V, $T_{J}=25$ ° ($V_{DS}=-20$ V, $V_{GS}=0$ V, $T_{J}=150$				-1.0 -10	μΑ
I _{GSS}	Gate-Body Leakage Current (V _{GS} = ±	20 V, V _{DS} = 0 V)			±100	nA
ON CHAR	ACTERISTICS (Note 2)					
V _{GS(th)}	Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = -250 \mu A$) (Negative Temperature Coefficient)	-1.1	-1.9 3.0	-2.3	V mV/°C
R _{DS(on)}	Static Drain-to-Source On-Resistance $(V_{GS} = -10 \text{ V}, I_D = -200 \text{ mA})$ $(V_{GS} = -4.5 \text{ V}, I_D = -50 \text{ mA})$			0.55 0.80	0.80 1.10	Ω
9fs	Forward Transconductance (V _{DS} = -10 V, I _D = -200 mA)			0.5		Mhos
DYNAMIC	CHARACTERISTICS		_			-
C _{iss}	Input Capacitance	(V _{DS} = -5.0 V, V _{GS} = 0 V, F = 1.0 MHz)		70		pF
Coss	Output Capacitance			74		1
C _{rss}	Reverse Transfer Capacitance			26		
SWITCHIN	IG CHARACTERISTICS (Note 3)					
t _{d(on)}	Turn-On Delay Time			3.0		ns
t _r	Rise Time	$(V_{DD} = -15 \text{ V}, I_D = -200 \text{ mA},$		6.0		
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = -10 \text{ V}, R_{G} = 6.0 \Omega$		18		
t _f	Fall Time			4		
Q_{TOT}	Total Gate Charge			2.18		nC
Q_{GS}	Gate-Source Charge	$(V_{DS} = -15 \text{ V}, I_D = -200 \text{ mA}, V_{GS} = -10 \text{ V})$		0.41		
Q_{GD}	Gate-Drain Charge	,		0.40		
BODY-DR	AIN DIODE CHARACTERISTICS (Note	2)				
V_{SD}	Diode Forward Voltage (Note 2) $(I_S = -400 \text{ mA}, V_{GS} = 0 \text{ V})$ $(I_S = -400 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 150 \text{ mA})$	0°C)		-0.8 -0.65	-1.0	V
t _{rr}	Reverse Recovery Time			11.8		ns
ta	1	$(I_S = -1.0 \text{ A}, V_{GS} = 0 \text{ V}, \\ dI_S/dt = 100 \text{ A}/\mu\text{s})$		9		1
t _b	1	3, 100 , 4, 4, 400,		3		1
Q_{RR}	Reverse Recovery Stored Charge	$(I_S = -1.0 \text{ A}, V_{GS} = 0 \text{ V}, \\ dI_S/dt = 100 \text{ A}/\mu\text{s})$		0.007		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤[300 µs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperature.

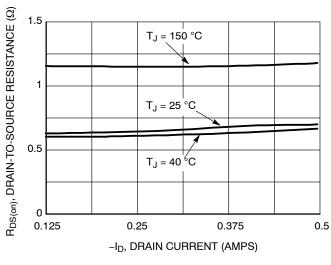
TYPICAL CHARACTERISTICS



 $V_{DS} \ge -10 \text{ V}$ V_{DS}

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



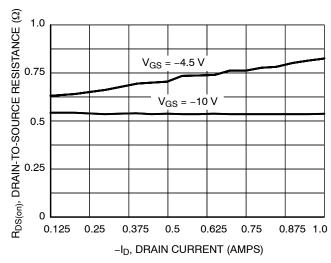
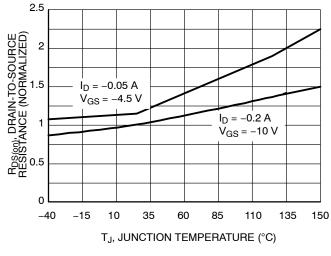


Figure 3. On-Resistance versus Drain Current

Figure 4. On-Resistance versus Drain Current and Gate Voltage



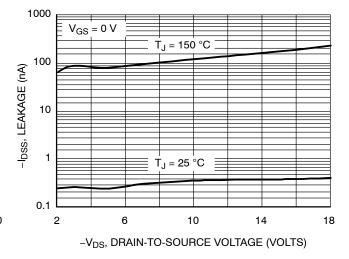


Figure 5. On-Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL CHARACTERISTICS (continued)

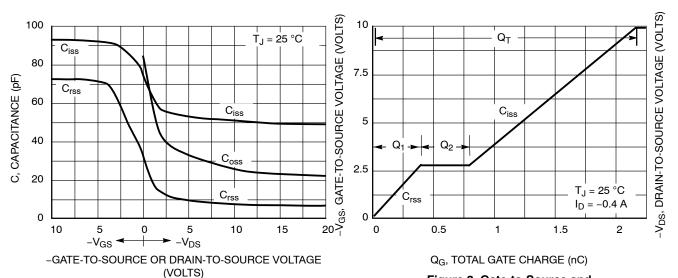


Figure 7. Capacitance Variation

Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

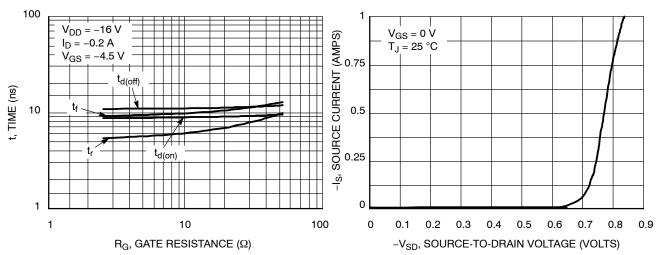


Figure 9. Resistive Switching Time Variation versus Gate Resistance

Figure 10. Diode Forward Voltage versus

Current

DEVICE ORDERING INFORMATION

Device	Package	Shipping [†]
NTR0202PLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

DISCONTINUED (Note 4)

NTR0202PLT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
NVTR0202PLT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

^{4.} **DISCONTINUED:** This device is not available. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

REVISION HISTORY

Revision	Description of Changes	Date
8	NVTR0202PLT1G OPN Marked as Discontinued.	7/15/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

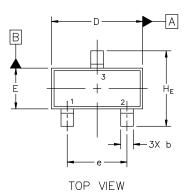
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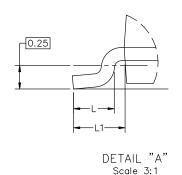
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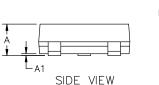
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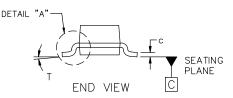
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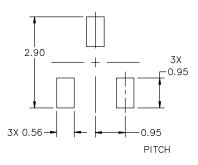
10°











NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Documen Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 1 OF 2	

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODI	
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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